Electronic Supplementary Material (ESI) for Nanoscale.

Supporting Informations

for

Nucleation and growth of stacking-dependent nanopores in bilayer *h*-BN

Tao Xu[1,*], Yizhi Tu[1], Yatong Zhu[1], Yuting Shen[2], Kuibo Yin[1], and Litao Sun[1,*]

[1]*SEU-FEI Nano-Pico Center, Key Lab of MEMS of Ministry of Education, Southeast University, Nanjing 210096, P. R. China*

[2]*College of Physics and Electronic Engineering, Changshu Institute of Technology, Changshu 215 500, P. R. China*

*Corresponding email: xt@seu.edu.cn, slt@seu.edu.cn

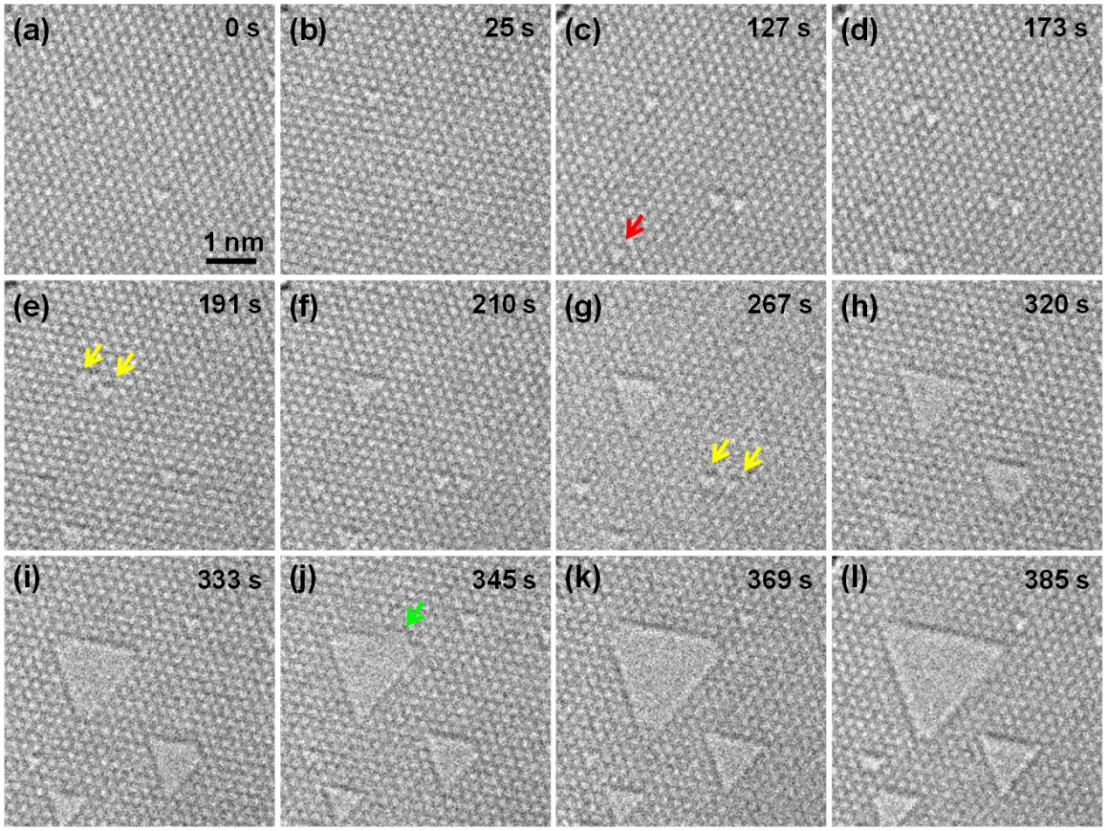

Fig.S1 Sequential TEM images showing the formation of pores from the nucleation of V_B under electron beam with current density of 480 A/cm^2. N-terminated triangular pores were unconditionally formed and the overall triangular shape was maintained. The triangular shape was maintained even after two pores merged together, and all pores have exactly the same orientation.

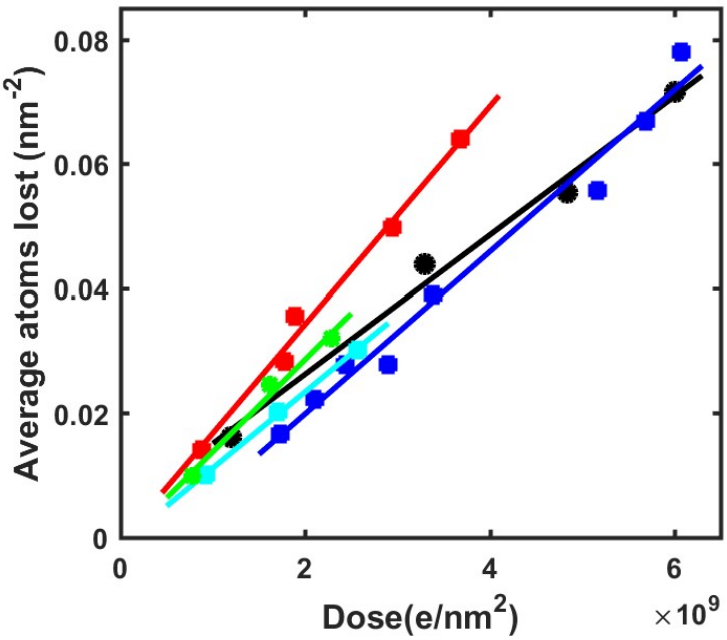

Fig.S2 Average atoms lost vs. dose trajectory plots of five samples.

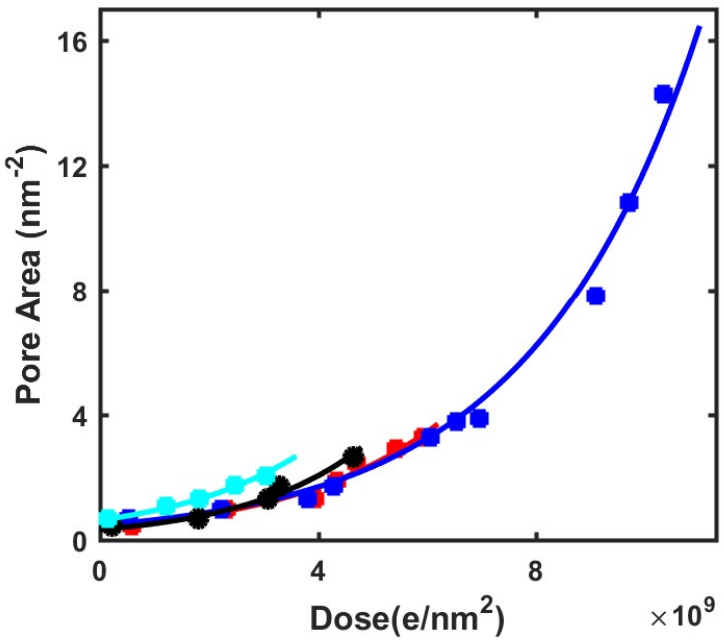

Fig.S3 Pore size vs. dose trajectory plots of four pores.

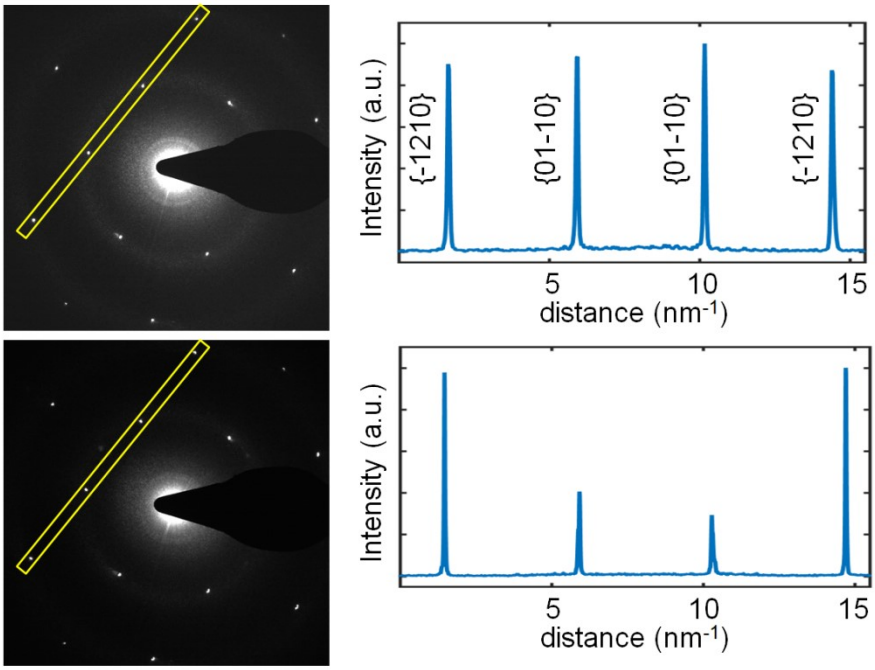

Fig.S4 Selected area electron diffraction of AA' and AB stacked *h*-BN bilayers.

Although the patterns look almost the same, the intensity profiles of diffraction spots are totally different. The $I_{\{01\text{-}10\}} / I_{\{\text{-}1210\}}$ ratio is 1.1 for AA' stacked bilayers and 0.35 for AB stacked bilayers.